

Silicon PNP Power Transistor

MJE253

DESCRIPTION

- Collector–Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = -100\text{ V}(\text{Min})$
- DC Current Gain-  
:  $h_{FE} = 40(\text{Min}) @ I_C = -0.2\text{ A}$
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = -0.3\text{V}(\text{Max.}) @ I_C = -0.5\text{ A}$
- Complement to Type MJE243

APPLICATIONS

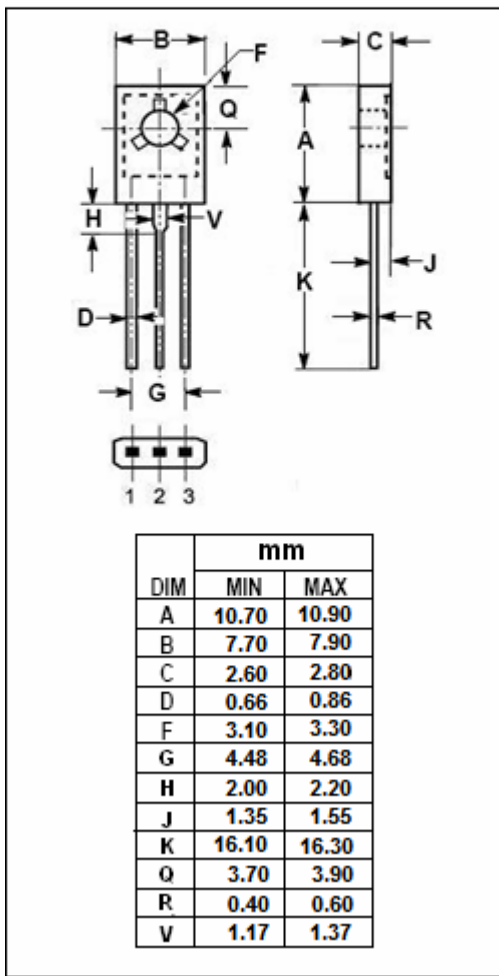
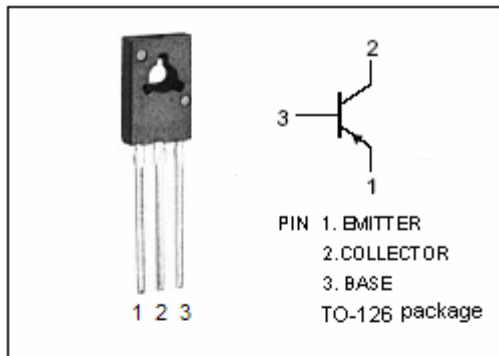
- Designed for low power audio amplifier and low-current, high-speed switching applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-100	V
$V_{EBO}$	Emitter-Base Voltage	-7	V
$I_C$	Collector Current-Continuous	-4	A
$I_{CM}$	Collector Current-Peak	-8	A
$I_B$	Base Current	-1	A
$P_C$	Collector Power Dissipation $T_a=25$	1.5	W
	Collector Power Dissipation $T_C=25$	15	
$T_j$	Junction Temperature	150	
$T_{stg}$	Storage Temperature Range	-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	8.34	/W
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	83.4	/W



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## ELECTRICAL CHARACTERISTICS

 $T_C = 25$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -10mA; I_B = 0$	-100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -0.5 A; I_B = -50mA$		-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -1A; I_B = -0.1A$		-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -2A; I_B = -0.2A$		-1.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -0.5A; V_{CE} = -1V$		-1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -100V; I_E = 0$ $V_{CB} = -100V; I_E = 0; T_C = 125$		-0.1 -0.1	$\mu A$ mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -7V; I_C = 0$		-0.1	$\mu A$
$h_{FE-1}$	DC Current Gain	$I_C = -0.2 A; V_{CE} = -1V$	40	180	
$h_{FE-2}$	DC Current Gain	$I_C = -1A; V_{CE} = -1V$	15		
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.1 A; V_{CE} = -10V; f_{test} = 10MHz$	40		MHz
$C_{OB}$	Collector Capacitance	$I_E = 0; V_{CB} = -10V; f_{test} = 0.1MHz$		50	pF